

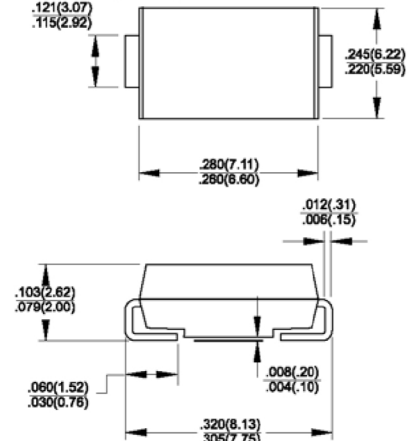
Features

- ◆ Glass passivated junction chip
- ◆ For surface mounted application
- ◆ Low profile package
- ◆ Built-in strain relief
- ◆ Ideal for automated placement
- ◆ Easy pick and place
- ◆ Superfast recovery time for high efficiency
- ◆ Glass passivated chip junction
- ◆ High temperature soldering:
250°C/10 seconds at terminals
- ◆ Plastic material used carries Underwriters Laboratory
Classification 94V-O

Mechanical Data

- ◆ Cases: Molded plastic
- ◆ Terminals: Solder plated
- ◆ Polarity: Indicated by cathode band
- ◆ Weight: 0.007 ounce, 0.21 gram

DO-214AB (SMC)



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Parameter	Symbols	ES 3A	ES 3B	ES 3C	ES 3D	ES 3F	ES 3G	ES 3J	ES 3K	ES 3M	Units	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	150	200	300	400	600	800	1000	Volts	
Maximum RMS voltage	V_{RMS}	35	70	105	140	210	280	420	560	700	Volts	
Maximum DC blocking voltage	V_{DC}	50	100	150	200	300	400	600	800	1000	Volts	
Maximum average forward rectified current See Fig. 1	I_{AV}						3.0					Amps
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) @ $T_J=100^\circ\text{C}$	I_{FSM}						100.0					Amps
Maximum instantaneous forward voltage @ 3.0A	V_F	0.95			1.3			1.7			Volts	
Maximum DC reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	I_R						10.0 500					μA μA
Maximum reverse recovery time (Note 1)	t_r						35					nS
Typical junction capacitance (Note 2)	C_J	50					40					pF
Typical thermal resistance (Note 3)	$R_{\theta JA}$ $R_{\theta JL}$						47 12					$^\circ\text{C}/\text{W}$
Operating junction temperature range	T_J						-55 to +150					$^\circ\text{C}$
Storage temperature range	T_{STG}						-55 to +150					$^\circ\text{C}$

Notes: 1. Reverse Recovery Test Conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$

2. Measured at 1 MHz and Applied $V_R=4.0$ Volts

3. Units Mounted on P.C.B. with 0.31 x 0.31" (8.0

($T_A = 25^\circ\text{C}$ unless otherwise noted)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

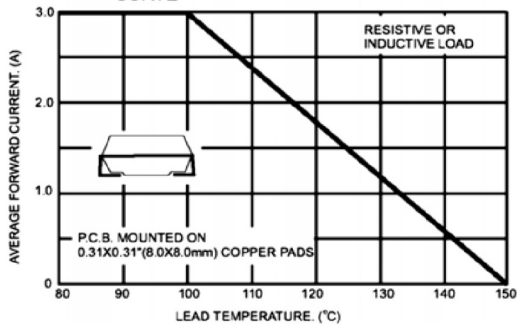


FIG.2- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

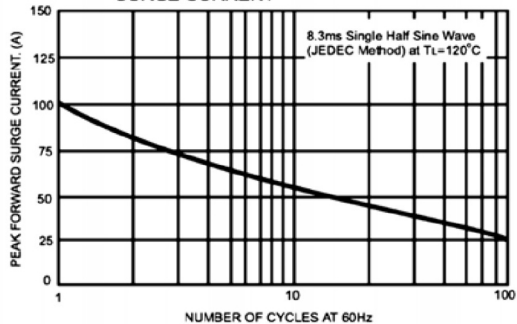


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

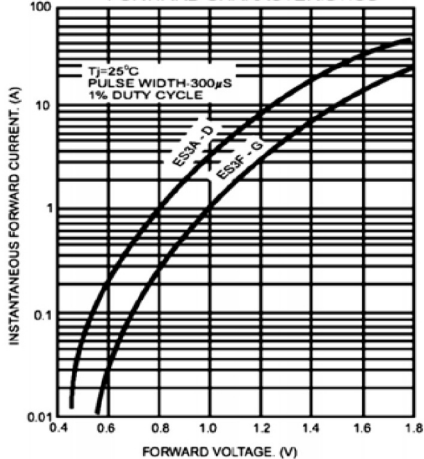


FIG.4- TYPICAL REVERSE CHARACTERISTICS

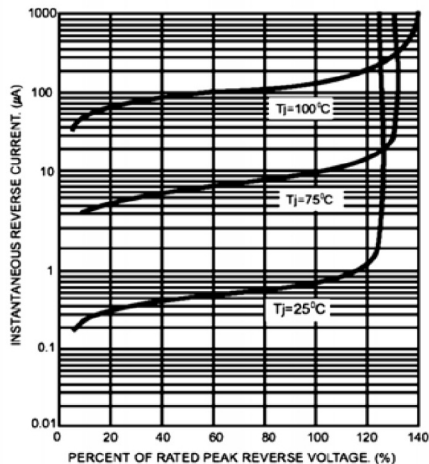
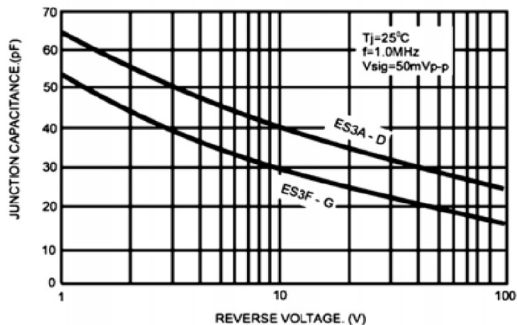


FIG.5- TYPICAL JUNCTION CAPACITANCE



单击下面可查看定价，库存，交付和生命周期等信息

[>>RCD\(达标电子\)](#)